

# HETERO JUNCTION FIELD EFFECT TRANSISTOR NE3508M04

# L TO S BAND LOW NOISE AMPLIFIER N-CHANNEL HJ-FET

### **FEATURES**

- Super low noise figure and high associated gain
   NF = 0.45 dB TYP., Ga = 14 dB TYP. @ f = 2 GHz, VDS = 2 V, ID = 10 mA
- Flat-lead 4-pin thin-type super minimold (M04) package

#### **APPLICATIONS**

- · Satellite radio (SDARS, DMB, etc.) antenna LNA
- · Low noise amplifier for microwave communication system

### **ORDERING INFORMATION**

Part Number	Order Number	Package	Quantity	Marking	Supplying Form
NE3508M04	NE3508M04-A	Flat-lead 4-pin thin-	50 pcs (Non reel)	V79	8 mm wide embossed taping
NE3508M04-T2	NE3508M04-T2-A	type super minimold (M04) (Pb-Free)	3 kpcs/reel		Pin 1 (Source), Pin 2 (Drain) face the perforation side of the tape

Remark To order evaluation samples, contact your nearby sales office.

Part number for sample order: NE3508M04

### ABSOLUTE MAXIMUM RATINGS (TA = +25°C)

Parameter	Symbol	Ratings	Unit
Drain to Source Voltage	Vos	4.0	V
Gate to Source Voltage	Vgs	-3.0	V
Drain Current	lσ	loss	mA
Gate Current	lg	400	μА
Total Power Dissipation	P <sub>tot</sub> Note	175	mW
Channel Temperature	Tch	+150	°C
Storage Temperature	T <sub>stg</sub>	-65 to +150	°C

Note Mounted on 1.08 cm<sup>2</sup> × 1.0 mm (t) glass epoxy PCB

Caution Observe precautions when handling because these devices are sensitive to electrostatic discharge.

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

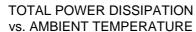
## RECOMMENDED OPERATING CONDITIONS (TA = +25°C)

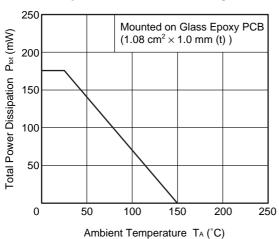
Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Drain to Source Voltage	Vos	-	2	3	V
Drain Current	lь	-	10	30	mA
Input Power	Pin	=	_	0	dBm

### ELECTRICAL CHARACTERISTICS (TA = +25°C, unless otherwise specified)

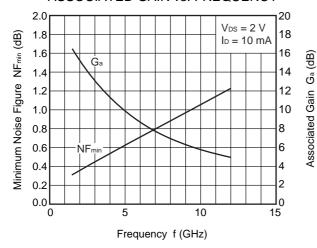
Parameter	Symbol	Test Conditions	MIN.	TYP.	MAX.	Unit
Gate to Source Leak Current	Igso	Vcs = −3 V	-	1	20	μА
Saturated Drain Current	IDSS	V <sub>DS</sub> = 2 V, V <sub>GS</sub> = 0 V	60	90	120	mA
Gate to Source Cutoff Voltage	VGS (off)	$V_{DS} = 2 \text{ V}, I_{D} = 100 \mu A$	-0.25	-0.5	-0.75	V
Transconductance	g <sub>m</sub>	V <sub>DS</sub> = 2 V, I <sub>D</sub> = 10 mA	100	_	-	mS
Noise Figure	NF	V <sub>DS</sub> = 2 V, I <sub>D</sub> = 10 mA, f = 2 GHz	-	0.45	0.7	dB
Associated Gain	Ga		12	14	-	dB
Gain 1 dB Compression	Po (1 dB)	V <sub>DS</sub> = 3 V, I <sub>D</sub> = 30 mA (Non-RF),	-	18	-	dBm
Output Power		f = 2 GHz				

### TYPICAL CHARACTERISTICS (TA = +25°C, unless otherwise specified)

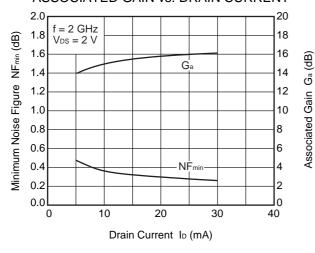




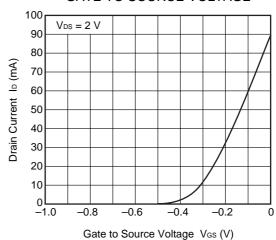
### MINIMUM NOISE FIGURE, ASSOCIATED GAIN vs. FREQUENCY



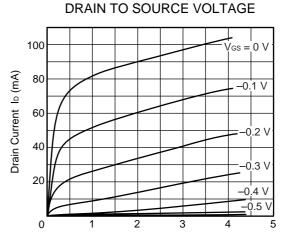
### MINIMUM NOISE FIGURE, ASSOCIATED GAIN vs. DRAIN CURRENT



# DRAIN CURRENT vs. GATE TO SOURCE VOLTAGE

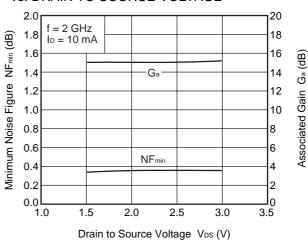


DRAIN CURRENT vs.



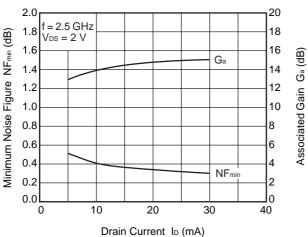
Drain to Source Voltage VDS (V)

# MINIMUM NOISE FIGURE, ASSOCIATED GAIN vs. DRAIN TO SOURCE VOLTAGE

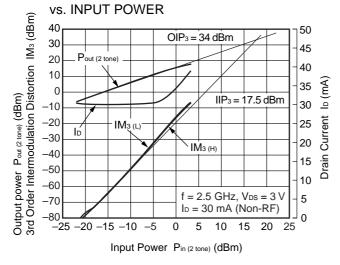


Remark The graphs indicate nominal characteristics.

### MINIMUM NOISE FIGURE, ASSOCIATED GAIN vs. DRAIN CURRENT

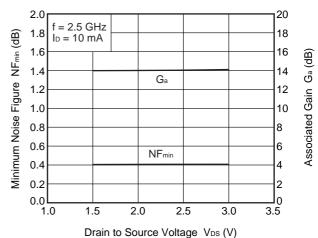


# OUTPUT POWER, IM3, DRAIN CURRENT



Remark The graphs indicate nominal characteristics.

# MINIMUM NOISE FIGURE, ASSOCIATED GAIN vs. DRAIN TO SOURCE VOLTAGE



### **S-PARAMETERS**

S-parameters/Noise parameters are provided on the NEC Compound Semiconductor Devices Web site in a form (S2P) that enables direct import to a microwave circuit simulator without keyboard input.

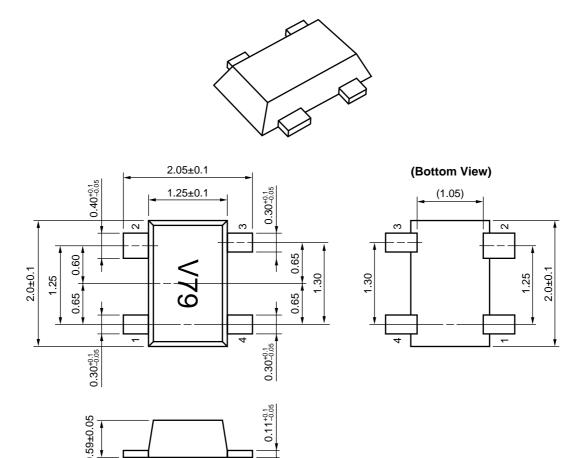
Click here to download S-parameters.

 $[\mathsf{RF} \ \mathsf{and} \ \mathsf{Microwave}] \to [\mathsf{Device} \ \mathsf{Parameters}]$ 

URL http://www.ncsd.necel.com/

### **PACKAGE DIMENSIONS**

### FLAT-LEAD 4-PIN THIN-TYPE SUPER MINIMOLD (M04) (UNIT: mm)

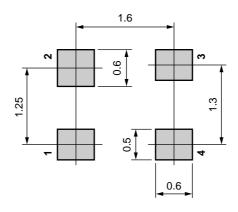


### **PIN CONNECTIONS**

- 1. Source
- 2. Drain
- 3. Source
- 4. Gate

### MOUNTING PAD DIMENSIONS (REFERENCE ONLY)

### FLAT-LEAD 4-PIN THIN-TYPE SUPER MINIMOLD (M04) PACKAGE (UNIT: mm)



### RECOMMENDED SOLDERING CONDITIONS

This product should be soldered and mounted under the following recommended conditions. For soldering methods and conditions other than those recommended below, contact your nearby sales office.

Soldering Method	Soldering Conditions		Condition Symbol
Infrared Reflow	Peak temperature (package surface temperature) Time at peak temperature Time at temperature of 220°C or higher Preheating time at 120 to 180°C Maximum number of reflow processes Maximum chlorine content of rosin flux (% mass)	: 260°C or below : 10 seconds or less : 60 seconds or less : 120±30 seconds : 3 times : 0.2%(Wt.) or below	IR260
Partial Heating	Peak temperature (terminal temperature) Soldering time (per side of device) Maximum chlorine content of rosin flux (% mass)	: 350°C or below : 3 seconds or less : 0.2%(Wt.) or below	HS350

Caution Do not use different soldering methods together (except for partial heating).



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Subject: Compliance with EU Directives

CEL certifies, to its knowledge, that semiconductor and laser products detailed below are compliant with the requirements of European Union (EU) Directive 2002/95/EC Restriction on Use of Hazardous Substances in electrical and electronic equipment (RoHS) and the requirements of EU Directive 2003/11/EC Restriction on Penta and Octa BDE.

CEL Pb-free products have the same base part number with a suffix added. The suffix –A indicates that the device is Pb-free. The –AZ suffix is used to designate devices containing Pb which are exempted from the requirement of RoHS directive (\*). In all cases the devices have Pb-free terminals. All devices with these suffixes meet the requirements of the RoHS directive.

This status is based on CEL's understanding of the EU Directives and knowledge of the materials that go into its products as of the date of disclosure of this information.

Restricted Substance per RoHS	Concentration Limit per RoHS (values are not yet fixed)	Concentration in CEL	on contained devices	
Lead (Pb)	< 1000 PPM	-A Not Detected	-AZ (*)	
Mercury	< 1000 PPM	Not Detected		
Cadmium	< 100 PPM	Not Detected		
Hexavalent Chromium	< 1000 PPM	Not Detected		
PBB	< 1000 PPM	Not Detected		
PBDE	< 1000 PPM	Not Detected		

If you should have any additional questions regarding our devices and compliance to environmental standards, please do not hesitate to contact your local representative.

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